

● Static Parameter Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	V	-20	—	—
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$	μA	—	—	-1.0
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	μA	—	—	± 20
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	V	-0.4	-0.74	-1.1
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-0.5A$	m Ω	—	480	500
		$V_{GS}=-2.5V, I_D=-0.5A$		—	640	750

● Dynamic Parameters (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Input Capacitance	C_{iss}	$V_{DS}=0V$ $V_{GS}=-16V$ $f=1MHz$	pF	—	113	—
Output Capacitance	C_{oss}			—	15	—
Reverse Transfer Capacitance	C_{rss}			—	9	—

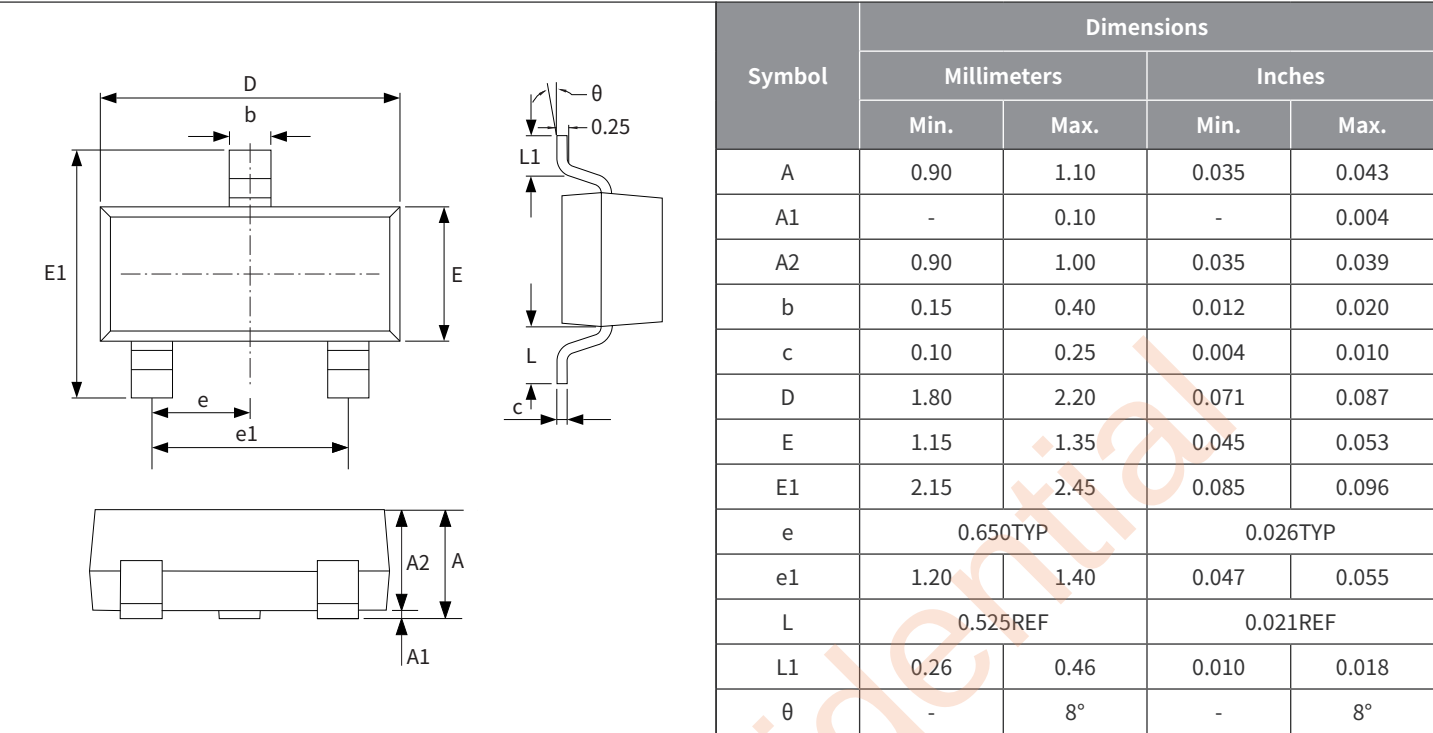
● Switching Parameters (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Total Gate Charge	Q_g	$V_{GS}=-4.5V$ $V_{DS}=-10V$ $I_D=-0.65A$	nC	—	1.24	—
Gate-Source Charge	Q_{gs}			—	0.37	—
Gate-Drain Charge	Q_{gd}			—	0.27	—
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=-4.5V$ $V_{DS}=-10V$ $I_D=-0.2A$ $R_{GEN}=10\Omega$	nS	—	9.0	—
Turn-on Rise Time	t_r			—	5.7	—
Turn-off Delay Time	$t_{D(off)}$			—	32.6	—
Turn-off fall Time	t_f			—	20.3	—

● Drian-Source Diode Characteristics

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Diode Forward Voltage	V_{SD}	$I_S=-0.66A, V_{GS}=0V$	V	—	—	-1.2
Maximum Body-Diode Continuous Current	I_S	—	A	—	—	-0.66

● Package Outline Dimensions (SOT-323)



● Suggested Pad Layout

